

Supporting Information

Langmuir-Blodgett Assembly of Bent-Shaped Rigid Amphiphiles into Spiral Rings

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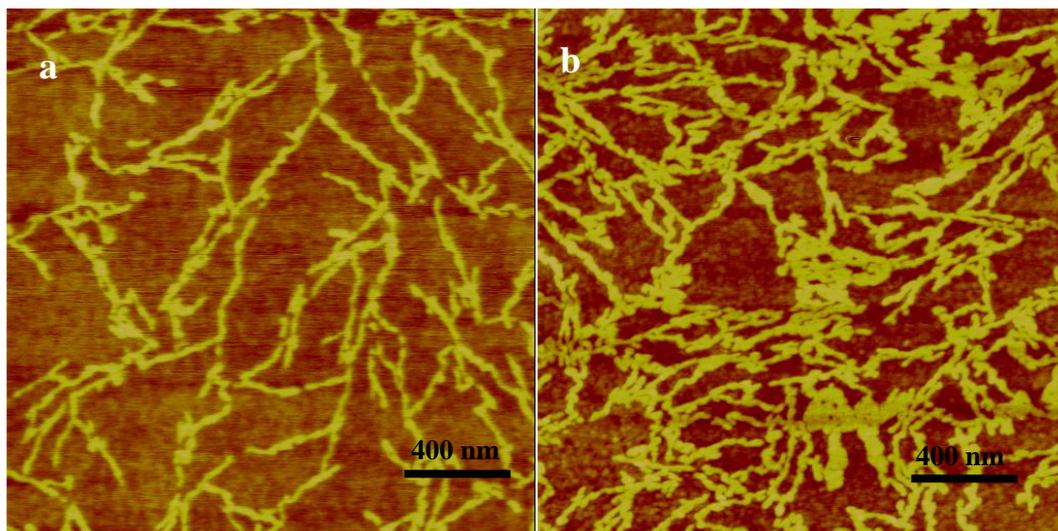


Fig. S1 AFM images the LB film of **1** deposited at the surface pressure of (a) 0.5 mN/m and (b) 5 mN/m.

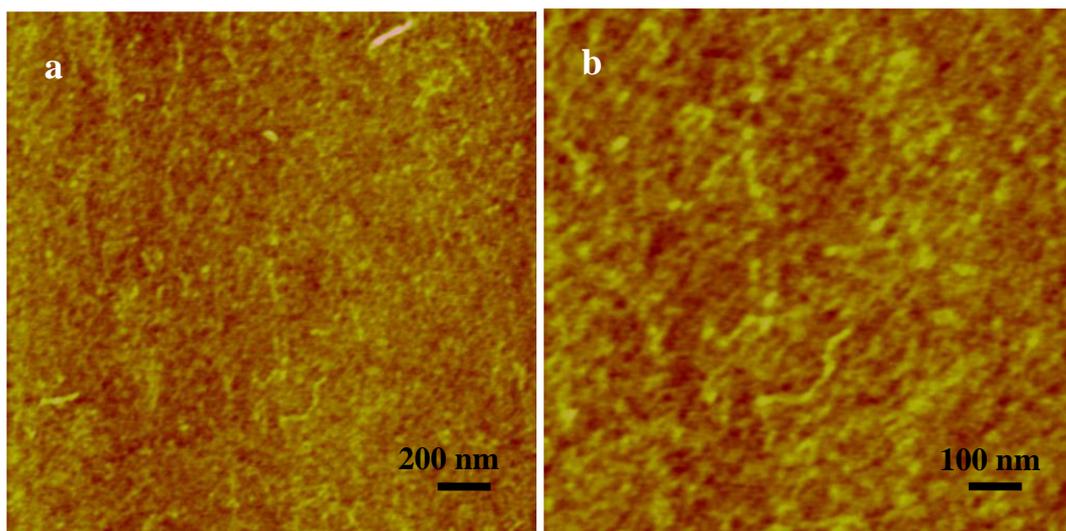


Fig. S2 AFM images of the LB films of **2** deposited at the onset of the surface pressure ($\pi < 0.02$ mN/m), (a) $2 \times 2 \mu\text{m}^2$ and (b) $1 \times 1 \mu\text{m}^2$ scan, respectively.

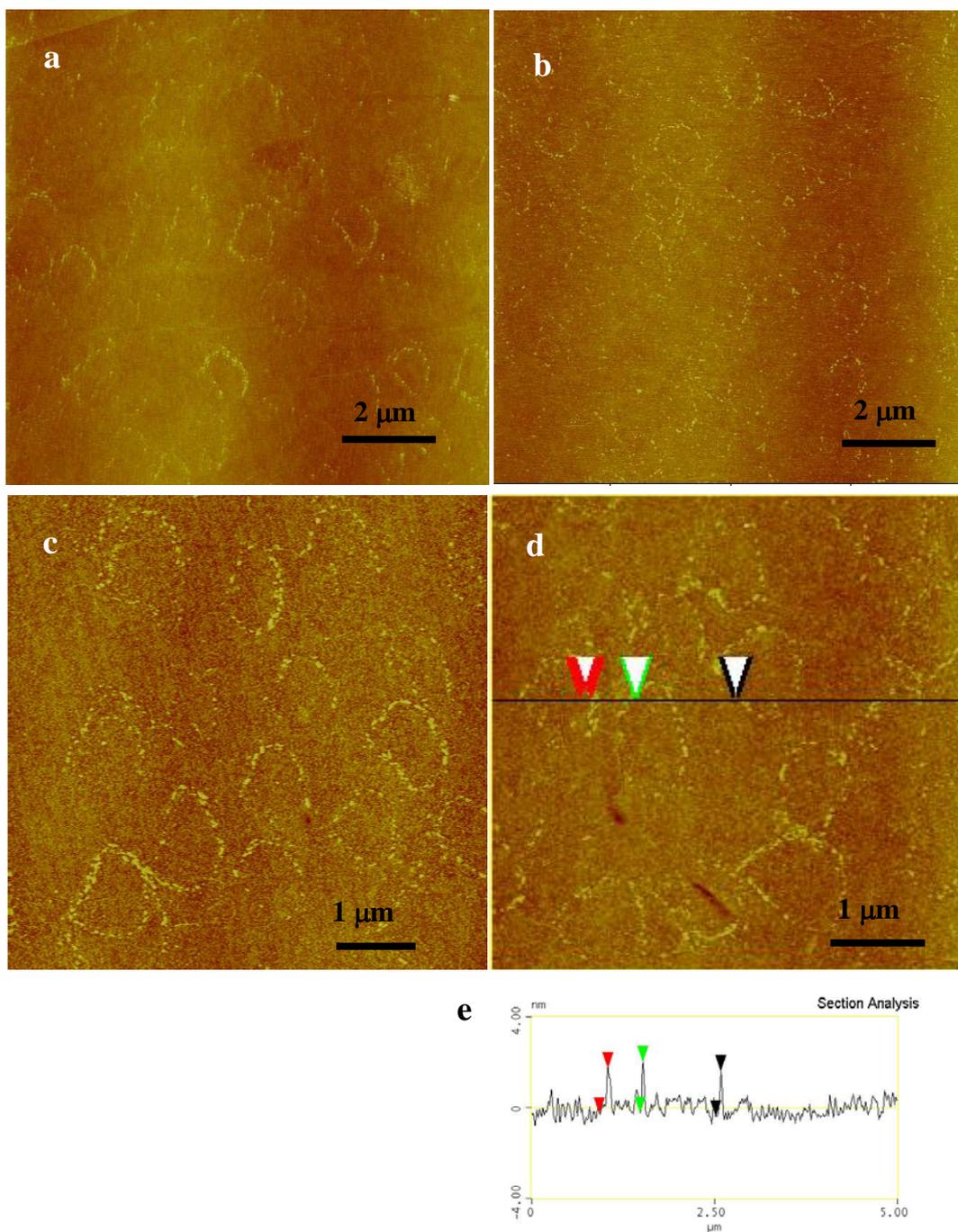


Fig. S3 AFM images of the LB films of **2** deposited at the surface pressure of 0.5 mN/m. The images were obtained by scan different area of the silicon wafer.

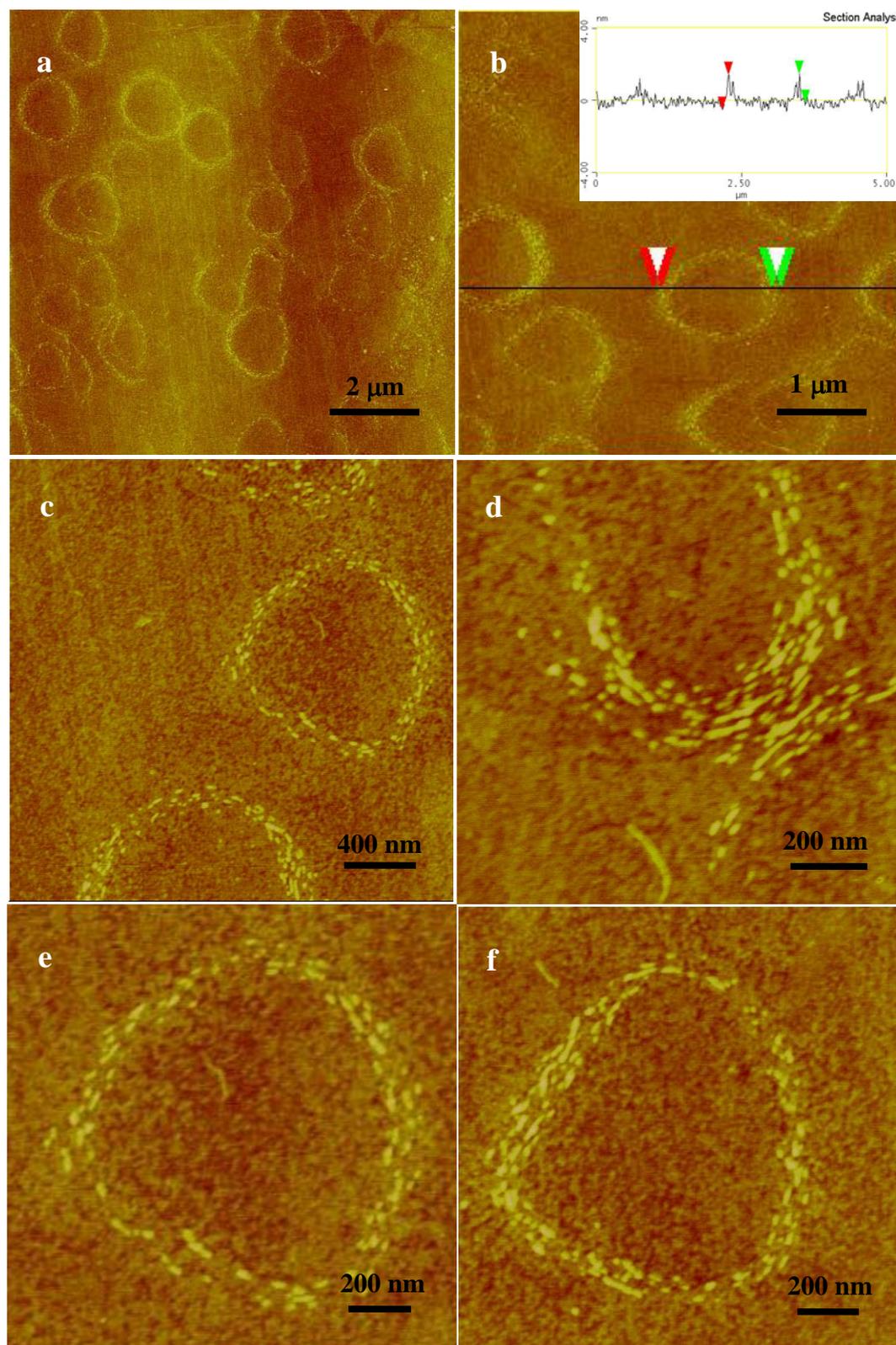


Fig. S4 AFM images of the LB films of **2** deposited at the surface pressure of 2 mN/m. (a) and (b) are different area of the silicon wafer; (c), (d), (e) and (f) are high resolution images.

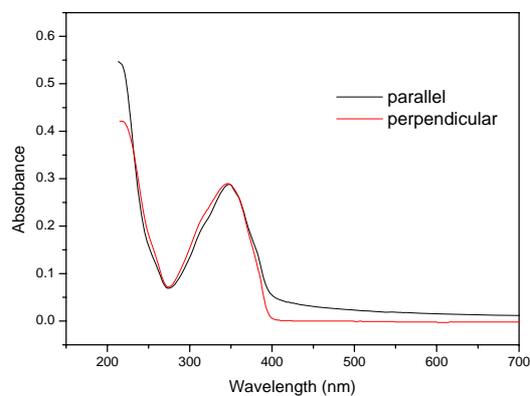


Fig. S5 Electronic spectrum in polarized light of the LB film of **2**: (black line) electric field vector parallel to the incidence plane; (red line) electric field vector perpendicular to the incidence plane.

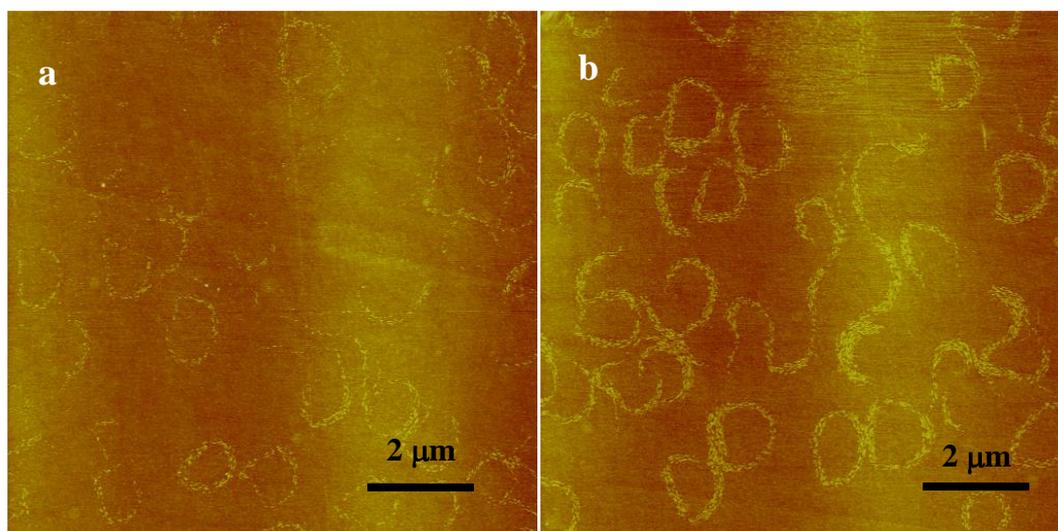


Fig. S6 AFM images of the LB films of **2** deposited at the rate of 40 mm/min, (a) at $\pi = 1$ mN/m and (b) $\pi = 3$ mN/m, respectively.

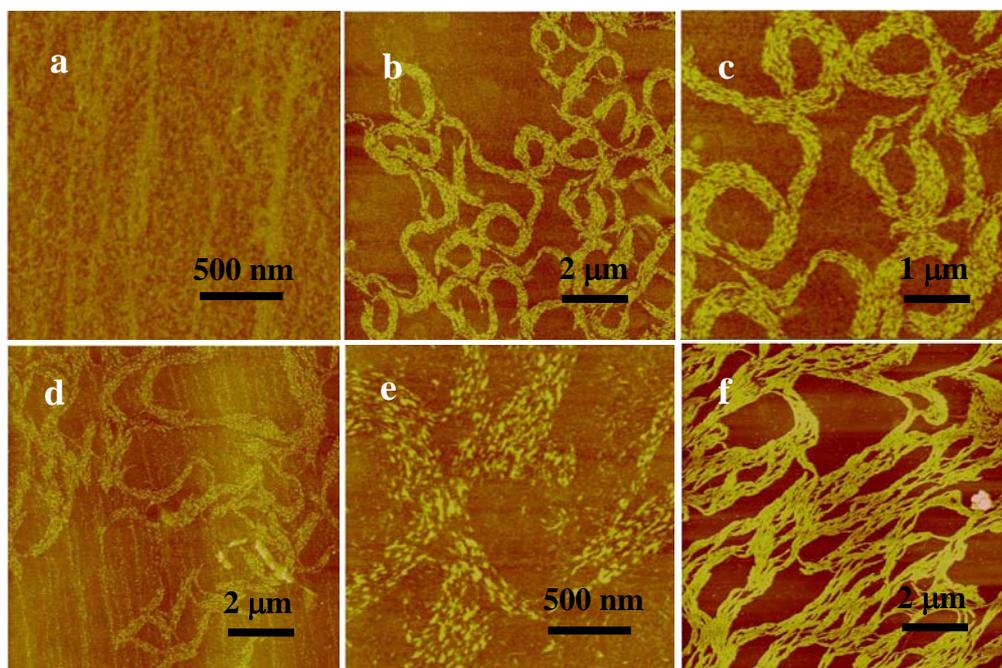


Fig. S7 AFM images of **3** deposited at the surface pressure of (a) 1 mN/m, (b) and (c) 5 mN/m, (d) and (e) 10 mN/m, (f) 20 mN/m, respectively.